



# Radiation Tolerance of the MUX64 for the High Granularity Timing Detector of ATLAS

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## Introduction

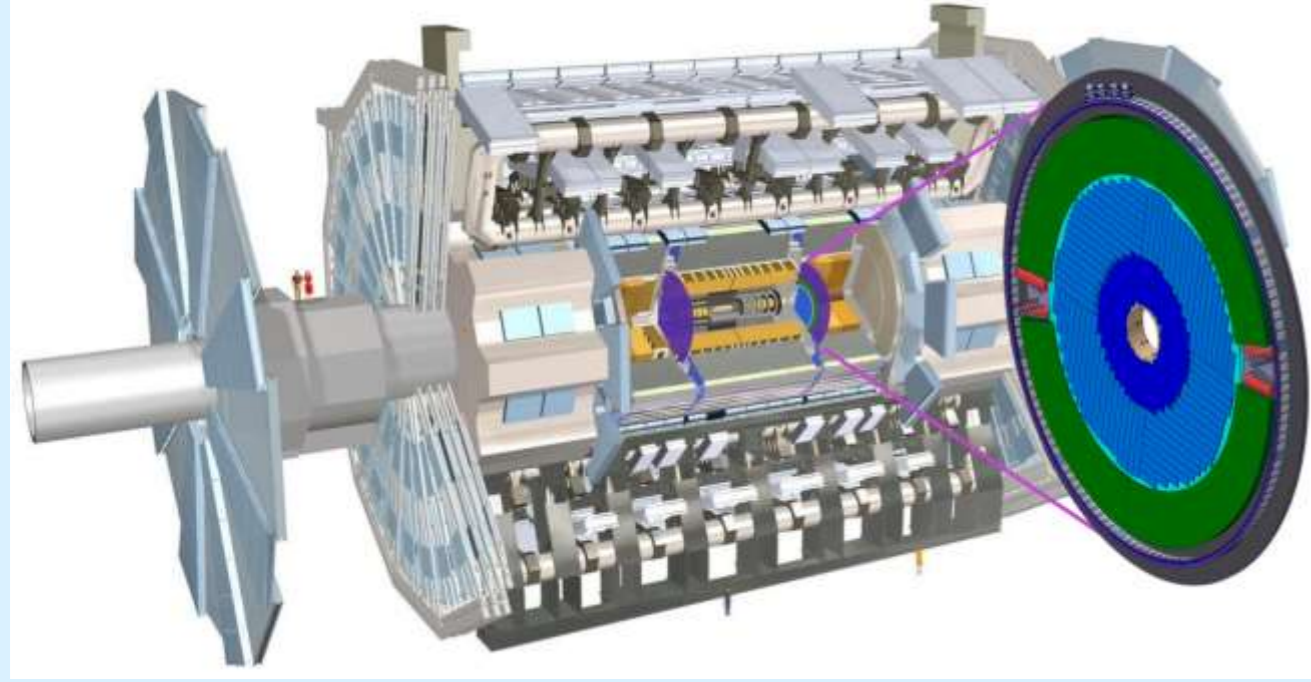
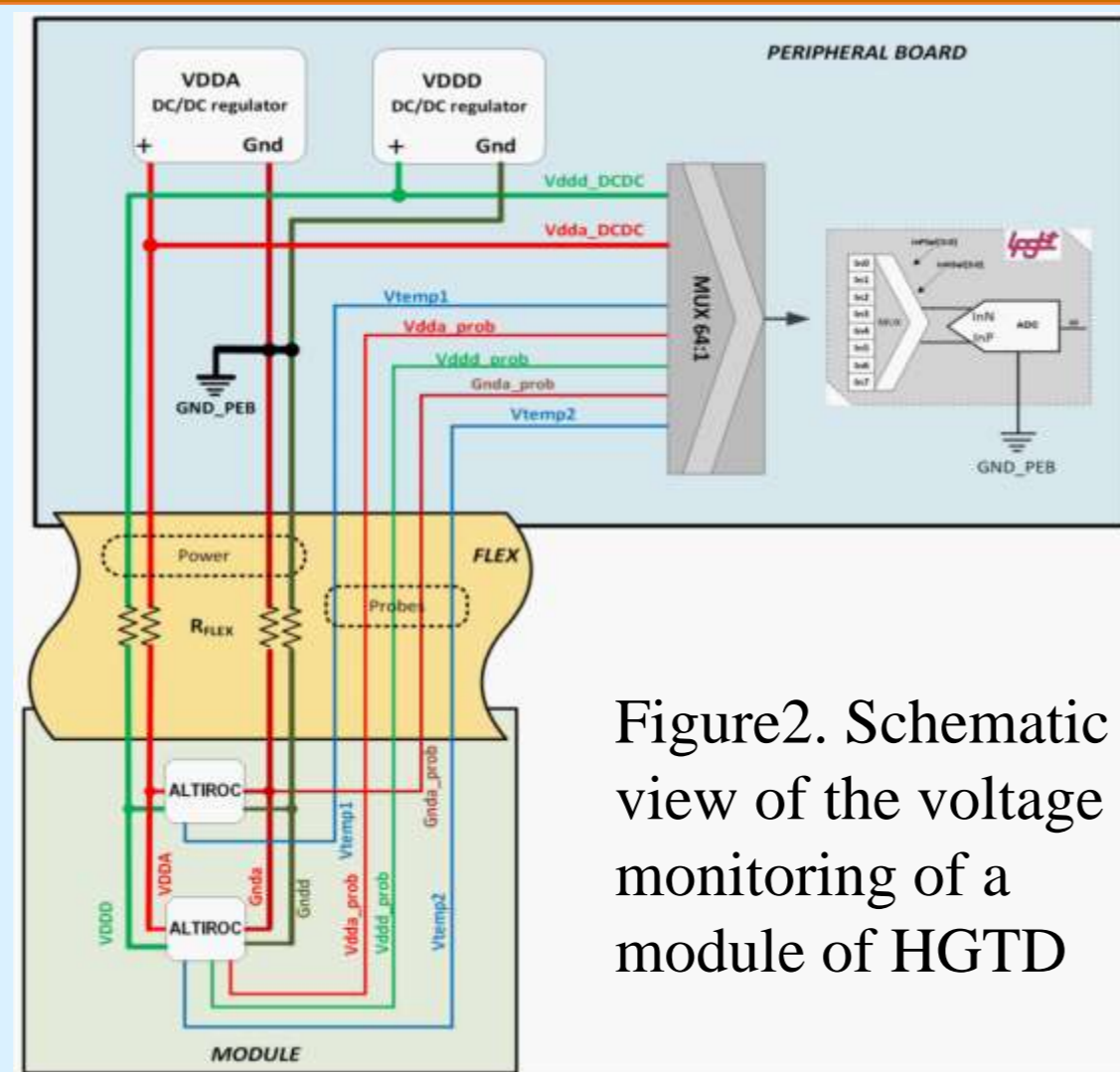


Figure1. Schematic of the ATLAS detector and the HGTD vessel



- The MUX64 ASIC is a 64-to-1 analog multiplexer developed for multiplexing of ADC input channels in the peripheral electronics of High Granularity Timing Detector (HGTD) for the ATLAS Phase-II upgrade.
- On-resistance ( $R_{on}$ ) of MUX64 is required to be lower than  $900 \Omega$  for matching the precision of the ADC, while off-resistance ( $R_{off}$ ) of MUX64 is required to be larger than  $60 M\Omega$ .<sup>[4]</sup>
- The MUX64 chips will be used in the radiation field of high-luminosity pp collisions at LHC to an integrated luminosity of  $4000 \text{ fb}^{-1}$  [2]. To verify the radiation tolerance of the MUX64, Non Ionizing Energy Loss (NIEL) and Total Ionizing Dose (TID) tests have been performed.
- The NIEL test was conducted with 80 MeV protons beam at APEP of CSNS<sup>[3]</sup>, two chips was irradiated to a fluence of  $3.21 \times 10^{15}$  (Si 1 MeV neq)/ $\text{cm}^2$ . The TID test was carried out in a MultiRad160 X-ray machine, five chips were irradiated to 0.746 MGy (Si) at a dose rate of 5.98 Gy/s (Si).

## Radiation tolerance requirements

### Radiation tolerance requirement

	Requirement (Ave of Genta and Fluka)	Requirement (Max of Genta and Fluka)	Test Dose
Total Ionizing Dose [Gy]	$4.71 \times 10^5$	$4.97 \times 10^5$	$7.46 \times 10^5$
1 MeV neutron equivalent [ $\text{cm}^2$ ]	$2.18 \times 10^{15}$	$2.18 \times 10^{15}$	$3.21 \times 10^{15}$

Table 1. TID and NIEL requirement and test results

- The  $R_{on}$  of MUX64 was measured to characterize the radiation damage.

### NIEL test setup

#### Parameters of the CSNS Proton Experiment Platform:

- Energy: 10-80 MeV; Beam Injection rate:  $10^5 - 10^{10}$  pps/ $\text{cm}^2$ .
- Beam spot size:  $10 \times 10 \text{ mm}^2 - 50 \times 50 \text{ mm}^2$  (continuously adjustable uniformity > 95%).



Figure 3. Photo of MUX64 at APEP

### NIEL test conditions

- Average injection proton rate:  $1.86 \times 10^9$  pps/ $\text{cm}^2$  (14.48 days in total).
- NIEL scale factor: 1.378 (for 80MeV proton to 1MeV neutron).
- Total equivalent fluence:  $3.21 \times 10^{15}$  (Si 1 MeV neq)/ $\text{cm}^2$ .

### TID test setup

#### Basic Parameters of MultiRad160 X-ray machine:

- Max voltage: 160 kV, Max current: 25 mA, max dose rate = 5 Gy/s (at positioned in air, 14.5 cm from the source).
- The MultiRad160 used in this test has been calibrated (in Si) by the ATLAS ITK strip group at 40 kV, 20 mA.<sup>[1]</sup>

### TID test conditions

- Dose rate: 5.98 Gy/s (in Si, 10 cm from source, 40kV, 20mA).
- Total irradiation dose: (35 h per chip)  $7.46 \times 10^5$  Gy.



Figure 4. MultiRad160 configuration

## NIEL and TID test results

### Technical procedure

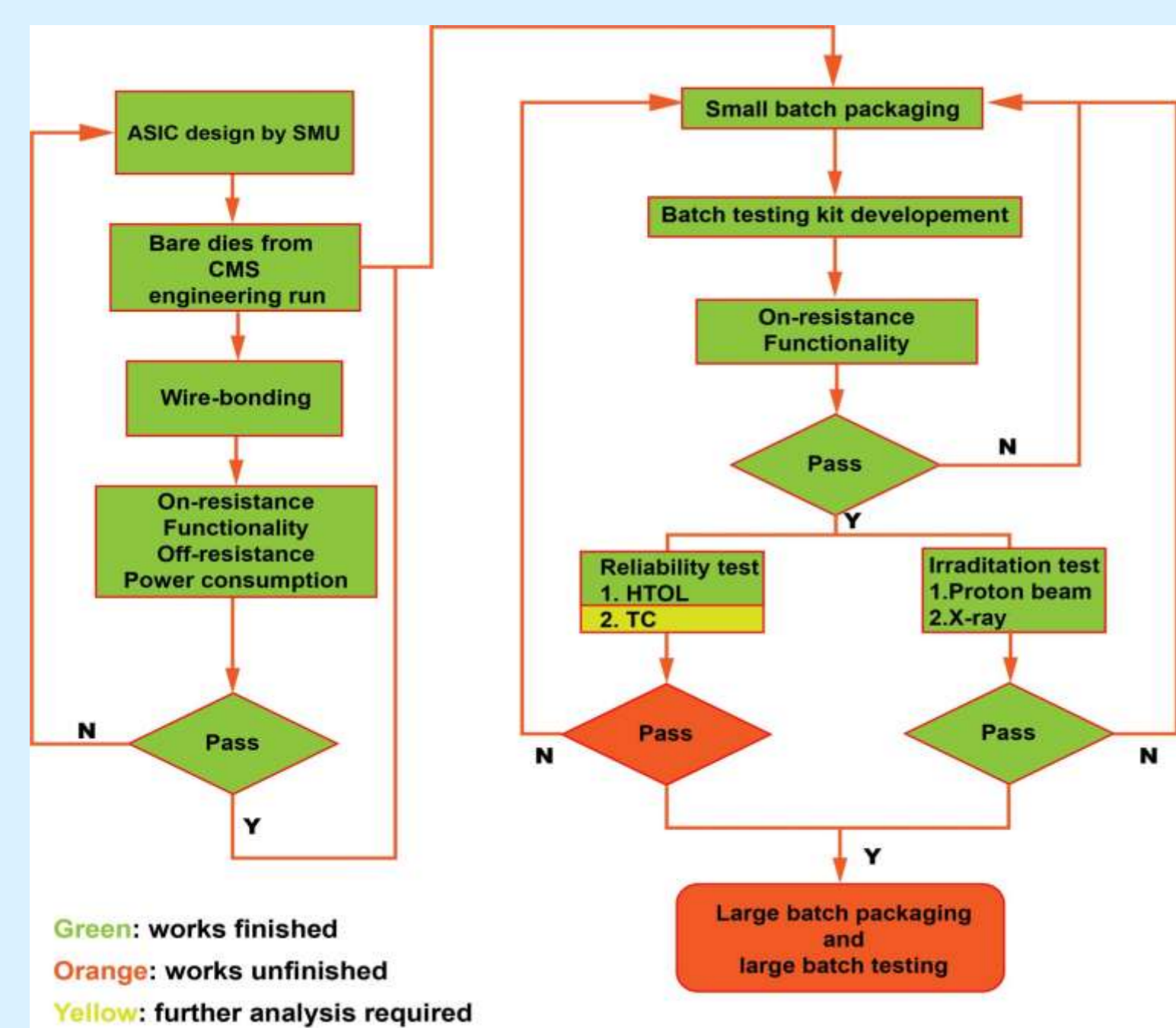
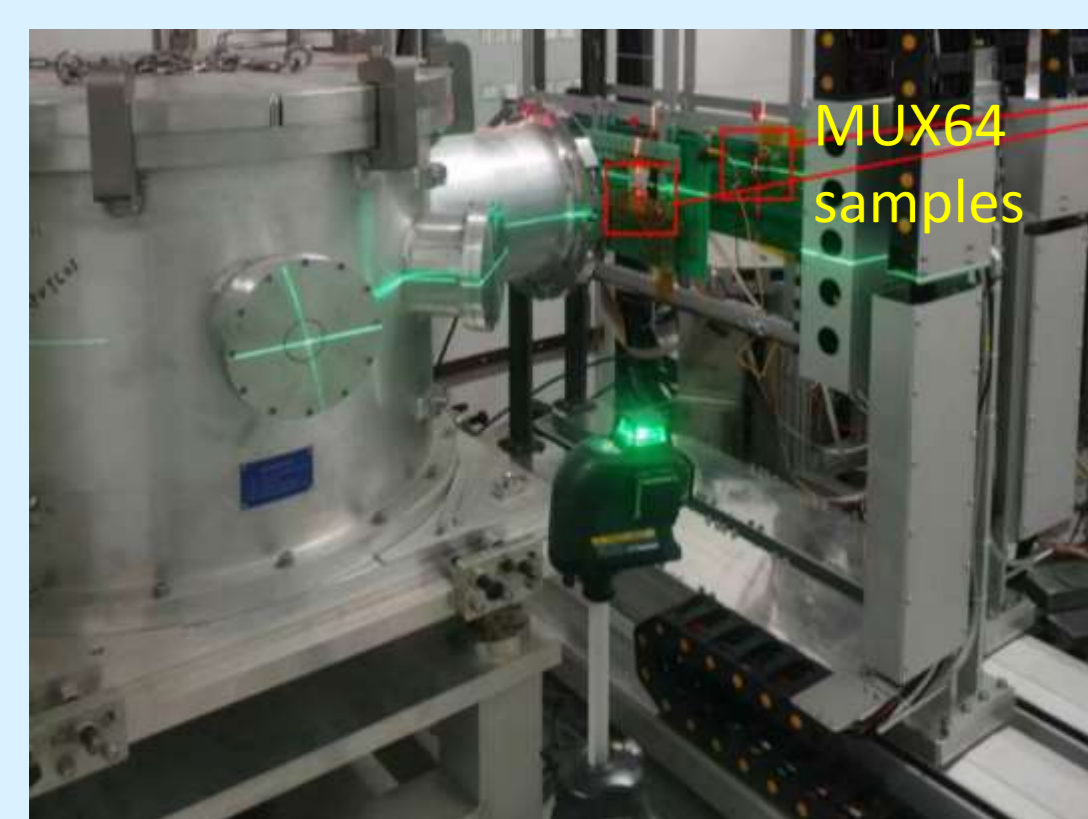


Figure4. Test procedure of MUX64. High Temperature Operating Life (HTOL), Temperature Cycling (TC).

### Result of NIEL test

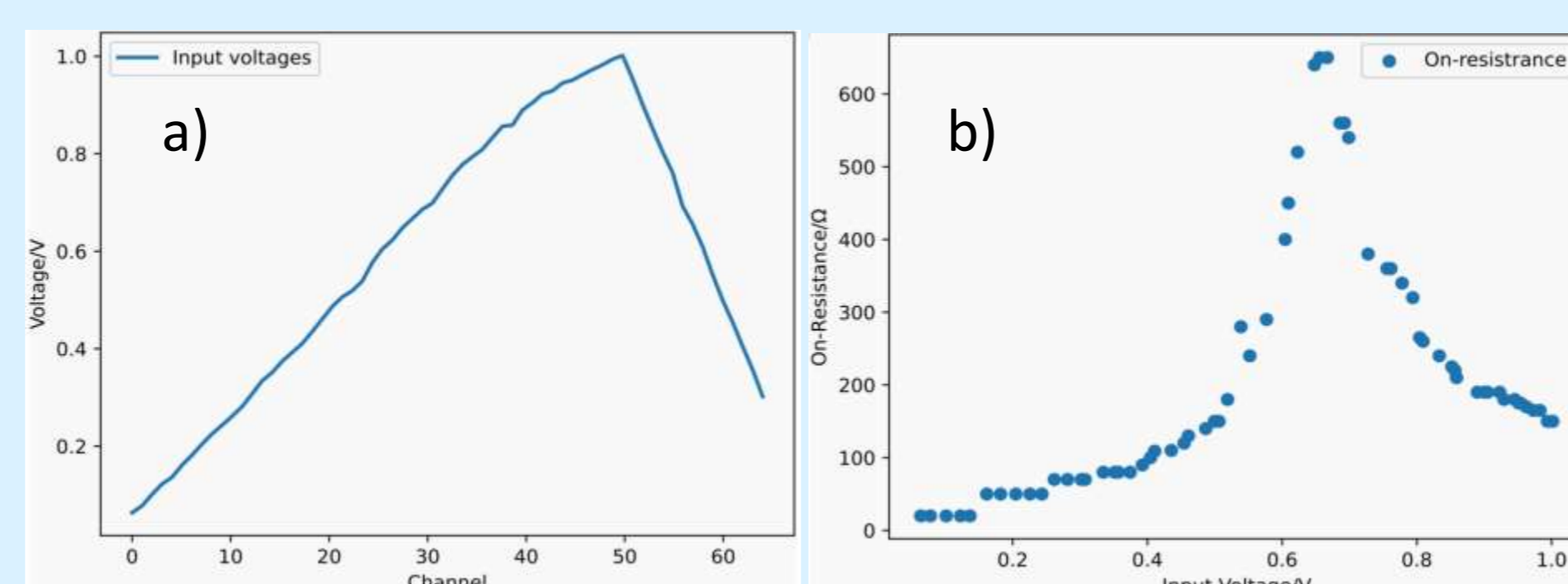


- Two MUX64 are tested simultaneously.
- Both chips are irradiated in the proton beam, positioned in sequence.

Figure5. MUX64s in NIEL test.

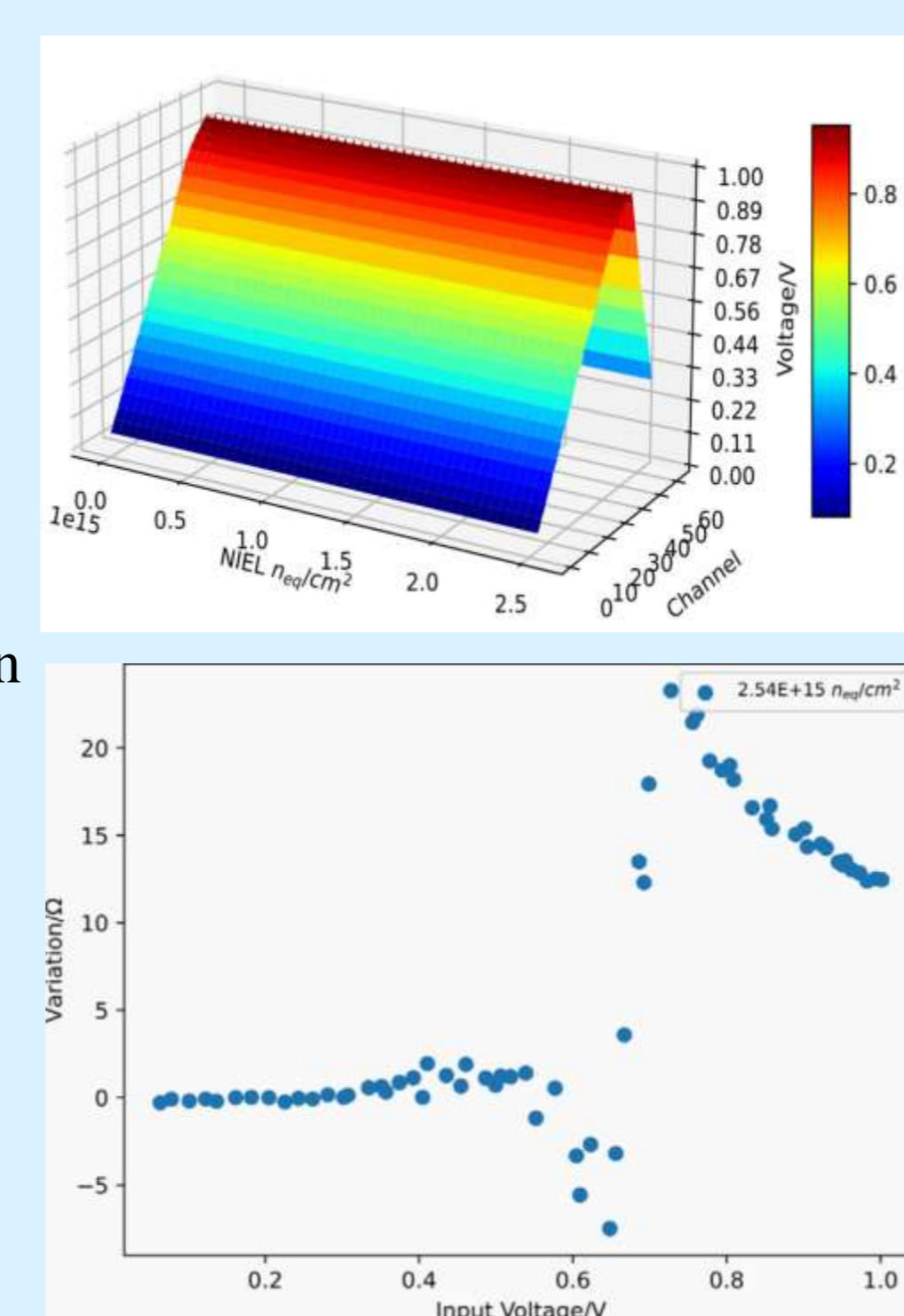
- A thin aluminum foil is attached to the front of the first MUX64 to measure the flux of proton.
- No accurate measurement for the flux nor the proton beam energy of the second MUX64.

### MUX64 before NIEL irradiation



- The spike near 0.65V in figure 6 (b) is because both MOSFETs of transmission gate in MUX64 are in partially conducting state.
- The  $R_{on}$  over 0-1V input voltage ( $V_{in}$ ) is required to be lower than  $900 \Omega$ . (Same as TID test)

### MUX64 performance after NIEL irradiation



- The smooth surface shown in Figure 7 indicates no channel misalignment during irradiation.

- Figure 8 shows the  $R_{on}$  variation ( $\Delta R_{on}$ ) versus  $V_{in}$  after the fluence of  $2.54 \times 10^{15}$  (1 MeV neq)/ $\text{cm}^2$ .
- The  $\Delta R_{on}$  after irradiation is less than  $25 \Omega$ .
- Two tested MUX64s show compatible performance.

Figure8.  $\Delta R_{on}$  versus  $V_{in}$  after irradiation.

### Result of TID test

- The MUX64s were irradiated one by one in the X-ray machine. In total five samples were tested.
- The MUX64 sample in X-ray cavity was supported 10 cm from the source.
- A 0.15 mm Al foil was applied to absorb low energy photons.
- Dose rate calibration had included the Al filter.
- The temperature in the X-ray chamber was not controlled.

### MUX64 before TID irradiation

- $R_{on}$  of each channel were measured with  $V_{in}$  ranging from 0.05V to 1.20V (step 0.05V).
- Figure 10. shows the expected  $R_{on}-V_{in}$  Curve.

### MUX64 performance after TID

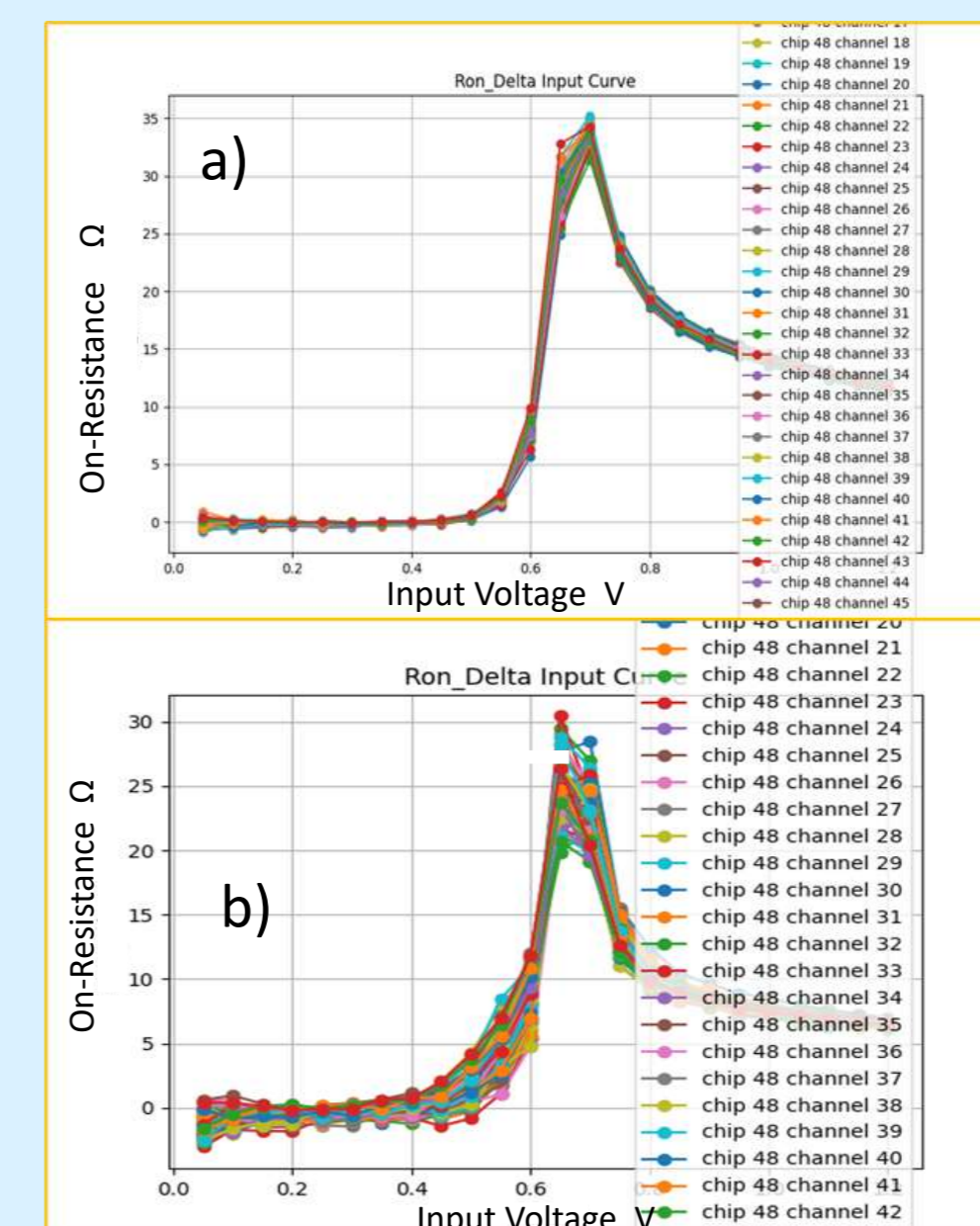


Figure11: (a)  $\Delta R_{on}$  after irradiation; (b)  $\Delta R_{on}$  after annealing.

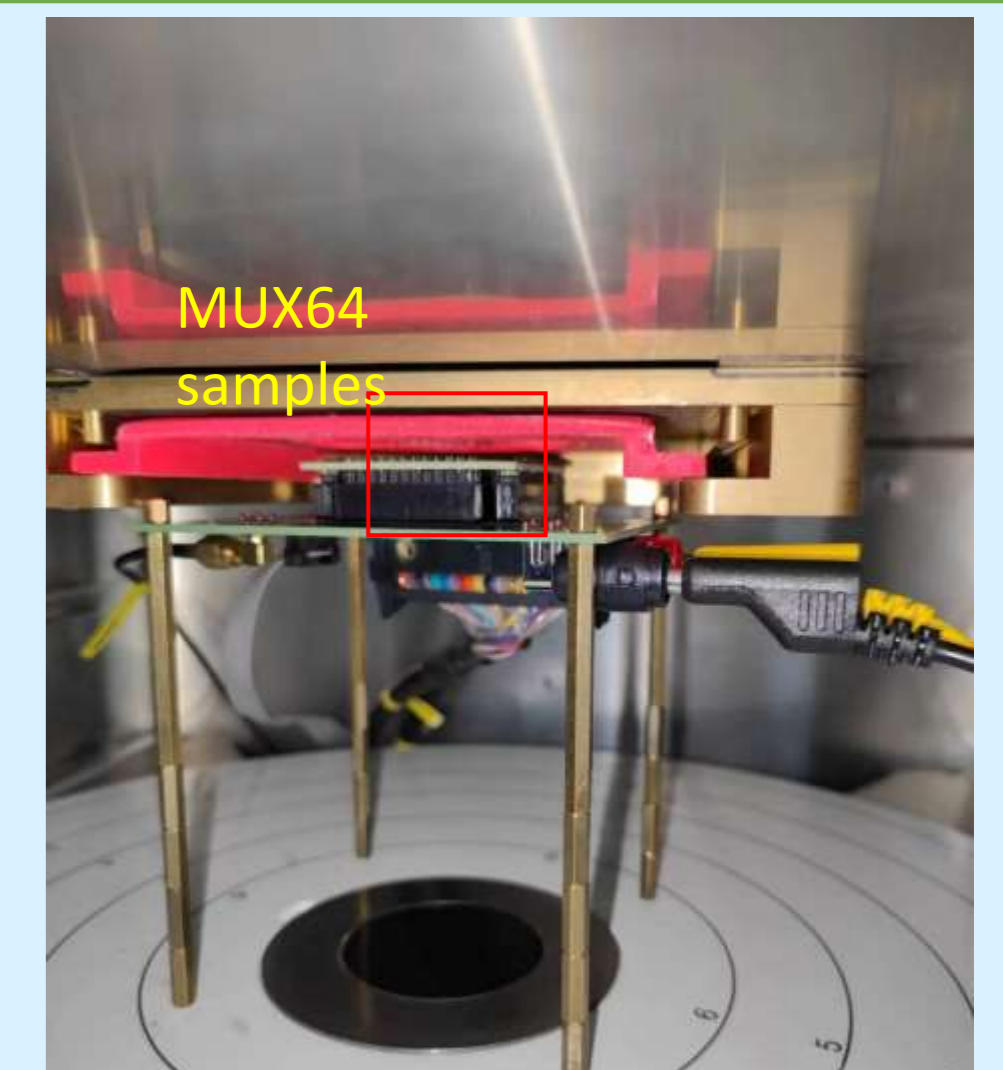


Figure9. MUX64 position in the X-ray cavity.

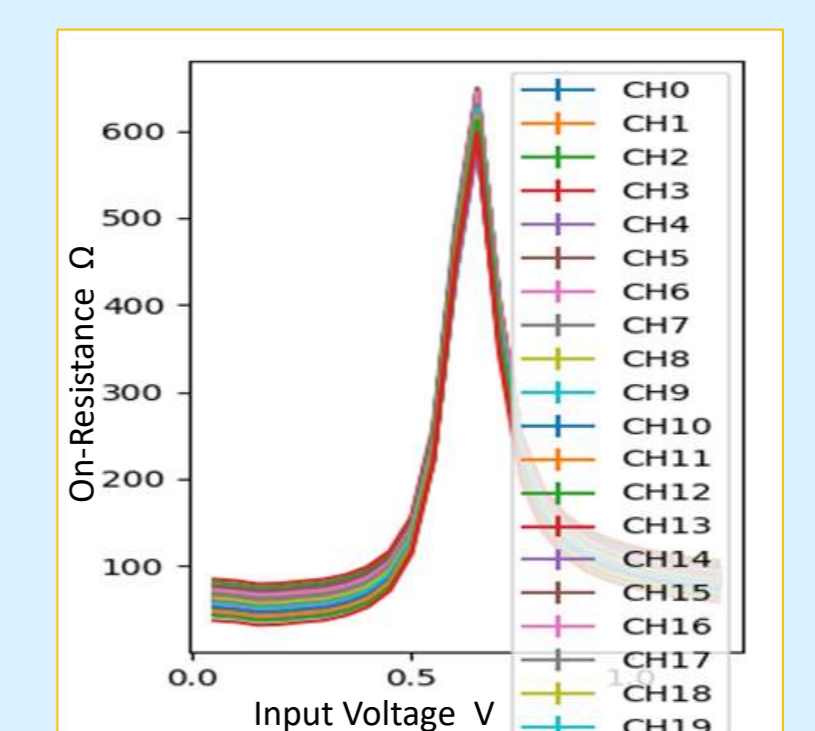


Figure10.  $R_{on}$  versus  $V_{in}$  before irradiation.

The  $R_{on}$  were measured for a typical (Chip-48) before irradiation at  $28.2^\circ\text{C}$ , after irradiation at  $26.5^\circ\text{C}$ , and after annealing at  $25.0^\circ\text{C}$ .

- The  $\Delta R_{on}$  after irradiation is less than  $35 \Omega$ .
- The  $\Delta R_{on}$  after annealing is less than  $30 \Omega$ .
- The other 4 chips have compatible performance after TID.

## Conclusion

- The radiation tolerance of MUX64 is verified. It is expected to function effectively in the high-luminosity environment of the HGTD for a service period corresponding to the accumulated luminosity of  $4000 \text{ fb}^{-1}$ .
- The MUX64 samples were irradiated by 80 MeV protons for NIEL effect equivalent  $3.21 \times 10^{15}$  (Si 1MeV neq)/ $\text{cm}^2$ , and X-ray for TID to 0.746 MGy (in Silicon). The multiplexing functionality shows negligible degradation for the radiation tolerance requirements of HGTD.

## Reference

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- [4] Z. Xu et al., MUX64, an analogue 64-to-1 multiplexer ASIC for the ATLAS high granularity timing detector, *2023 JINST* 18 C03012